

SOLID STATE DEVICES, INC.

14005 Stage Road * Santa Fe Springs, Ca 90670 Phone: (562) 404-4474 * Fax: (562) 404-1773

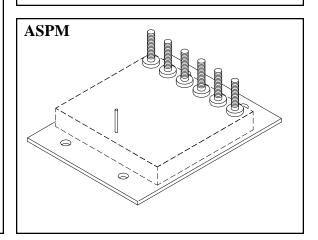
DESIGNER'S DATA SHEET

FEATURES:

- High Current Switching for Motor Drives and Inverters for Space Applications.
- Push-Pull Configuration with Freewheeling Diodes.
- Low Saturation Voltage at High Currents.
- Low Mechanical Stress Design.
- Hermetic Sealed Construction for Aerospace Applications.
- Excellent Thermal Management.
- Full Power Screened Hermetic Discretes.
- TX, TXV, and S-Level Screening Available.
- Consult Factory for:
 - Faster Switching Speeds;
 - Other Bridge Configurations and Terminal Styles.

SPMQ461-01

200 AMP/600 VOLTS
HALF BRIDGE
IGBT POWER MODULE
FOR SPACE APPLICATIONS



MAXIMUM RATINGS			
CHARACTERISTIC	SYMBOL	VALUE	UNIT
Collector to Emiter Voltage, per Leg	$ m V_{CES}$	600	Volts
Gate to Collector Voltage	$ m V_{GES}$	±20	Volts
Continuous Collector Current, per Leg $T_B = 25^{\circ}C$ $T_B = 90^{\circ}C$	I _{C1} I _{C2}	200 100	Amps
Pulse Collector Current, per Leg 1/	I_{CM}	300	Amps
Clamped Inductive Load Current, per Leg ($T_B = 125$ °C, $V_{CC} = 480$ V, $V_{GE} = 15$ V, $L = 30$ uH, $R_G = 10\Omega$	${ m I_{LM}}$	100	Amps
Reverse Voltage Avalange Energy, per Leg 1/(I _C = 100A)	$\mathbf{E}_{\mathbf{ARV}}$	5.6	mJ
Operating and Storage Temperature	T _{OP} & T _{STG}	-55 TO +150	°C
Thermal Resistance, Junction to Base, per Leg	$\Theta_{\mathbf{JB}}$	0.28	°C/W
Total Module Dissipation, per Leg @ $T_B = 25^{\circ}C$ Dissipation Derating from $T_B = 25^{\circ}C$ to $T_B = 150^{\circ}C$, per Leg	P _{D1} P _{D2}	625 5	W W/°C

1/ Pulse Duration Limited by T_{JMAX}; Repetative Rating

ELECTRICAL SCHEMATIC G Q1 C11 C12 C12 C21 C22

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ELECTRICAL CHARACTERISTICS @ T _J =25°C, per Leg (Unless Otherwise Specified)					
RATING	SYMBOL	MIN	MAX	UNIT	
	BV _{CES}	600	-	Volts	
	V _{GE(th)}	2.0	6	Volts	
	V _{CE(sat)2} V _{CE(sat)1}	-	3.1 2.5	Volts	
Gate-Emitter Leakage Current $(V_{GE} = \pm 20V, V_{CE} = 0V)$	I _{GES}	-	2.0	μAmps	
	I _{CES1} I _{CES1}	-	225 20	µAmps mAmps	
$ \begin{array}{c} \textbf{Anti-Parallel Diode Forward Voltage} \\ (I_F = 100A, T_B = 25^{\circ}C) \end{array} $	$\mathbf{V_F}$	-	1.6	Volts	
Insulation Resistance (All terminals to Base @1500V)	R _{INSUL1}	1	-	GΩ	

